



ISOLATED 3.3-V HALF AND FULL-DUPLEX RS-485 TRANSCEIVERS

Check for Samples: [ISO15](#), [ISO35](#), [ISO15M](#), [ISO35M](#)

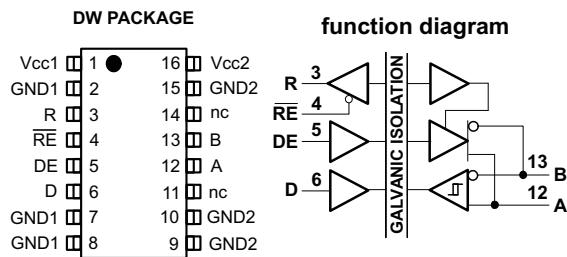
FEATURES

- 4000-V_{PK} V_{IOTM}, 560-V_{PK} V_{IORM} per IEC 60747-5-2 (VDE 0884, Rev 2)
- UL 1577, IEC 61010-1, IEC 60950-1 and CSA Approved
- 1/8 Unit Load – Up to 256 Nodes on a Bus
- Meets or Exceeds TIA/EIA RS-485 Requirements
- Signaling Rates up to 1 Mbps
- Thermal Shutdown Protection
- Low Bus Capacitance – 16 pF (Typ)
- 50 kV/μs Typical Transient Immunity
- Fail-safe Receiver for Bus Open, Short, Idle
- 3.3-V Inputs are 5-V Tolerant

APPLICATIONS

- Security Systems
- Chemical Production
- Factory Automation
- Motor/motion Control
- HVAC and Building Automation Networks
- Networked Security Stations

ISO15



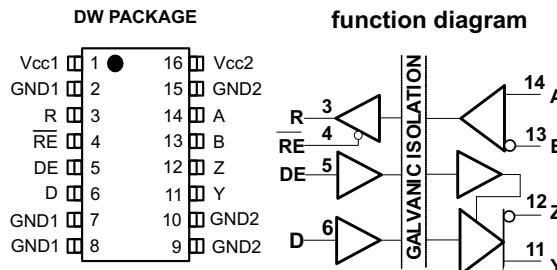
DESCRIPTION

The ISO15 is an isolated half-duplex differential line transceiver while the ISO35 is an isolated full-duplex differential line driver and receiver for TIA/EIA 485/422 applications. The ISO15M and ISO35M have extended ambient temperature ratings of -55°C to 125°C while the ISO15 and ISO35 are specified over -40°C to 85°C .

These devices are ideal for long transmission lines since the ground loop is broken to allow for a much larger common-mode voltage range. The symmetrical barrier of the device is tested to provide isolation of 4000 V_{PK} per VDE and 2500 V_{RMS} per UL and CSA between the bus-line transceiver and the logic-level interface.

Any cabled I/O can be subjected to electrical noise transients from various sources. These noise transients can cause damage to the transceiver and/or near-by sensitive circuitry if they are of sufficient magnitude and duration. These isolated devices can significantly increase protection and reduce the risk of damage to expensive control circuits.

ISO35



PRODUCT	FOOTPRINT	TEMP RATING	MARKING
ISO15	Half Duplex	-40°C to 85°C	ISO15
ISO35	Full Duplex	-40°C to 85°C	ISO35
ISO15M	Half Duplex	-55°C to 125°C	ISO15M
ISO35M	Full Duplex	-55°C to 125°C	ISO35M



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

			VALUE	UNIT
V _{CC}	Input supply voltage. ⁽²⁾ V _{CC1} , V _{CC2}		-0.3 to 6	V
V _O	Voltage at any bus I/O terminal		-9 to 14	V
V _{IT}	Voltage input, transient pulse, A, B, Y, and Z (through 100Ω, see Figure 11)		-50 to 50	V
V _I	Voltage input at any D, DE or \overline{RE} terminal		-0.5 to 7	V
I _O	Receiver output current		±10	mA
ESD Electrostatic discharge	Human Body Model	JEDEC Standard 22, Test Method A114-C.01	Bus pins and GND1	±6
			Bus pins and GND2	±16
			All pins	±4
	Charged Device Model	JEDEC Standard 22, Test Method C101	All pins	±1
	Machine Model	ANSI/ESDS5.2-1996		±200
T _J	Maximum junction temperature		170	°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values

RECOMMENDED OPERATING CONDITIONS

		MIN	TYP	MAX	UNIT
V _{CC}	Supply Voltage, V _{CC1} , V _{CC2}	3.15	3.3	3.6	V
V _{OC}	Voltage at either bus I/O terminal	A, B	-7	12	V
V _{IH}	High-level input voltage	D, DE, \overline{RE}	2	V _{CC}	V
V _{IL}	Low-level input voltage		0		
V _{ID}	Differential input voltage	A with respect to B	-12	12	V
R _L	Differential input resistance		54	60	Ω
I _O	Output current	Driver	-60	60	mA
		Receiver	-8	8	
1/t _{UI}	Signaling rate	ISO15x and ISO35x		1	Mbps
T _A	Ambient temperature	ISO15 and ISO35	-40	85	°C
		ISO15M and ISO35M	-55	125	
T _J	Operating junction temperature	ISO15 and ISO35	-40	150	°C
		ISO15M and ISO35M	-55	150	

SUPPLY CURRENT

over recommended operating condition (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{CC1}	Logic-side supply current	\overline{RE} at 0 V or V _{CC} , DE at 0 V, No load (driver disabled)			8	mA
		\overline{RE} at 0 V or V _{CC} , DE at V _{CC} , No Load (driver enabled)			8	
I _{CC2}	Bus-side supply current	\overline{RE} at 0 V or V _{CC} , DE at 0 V, No load (driver disabled)			15	mA
		\overline{RE} at 0 V or V _{CC} , DE at V _{CC} , No Load (driver enabled)			19	

DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$ V_{OD} $	Differential output voltage magnitude	$I_O = 0 \text{ mA}$, no load	2.5		V_{CC}	V
		$R_L = 54 \Omega$, See Figure 1	1.5	2		
		$R_L = 100 \Omega$ (RS-422), See Figure 1	2	2.3		
		V_{test} from -7 V to $+12 \text{ V}$, See Figure 2	1.5			
$\Delta V_{OD} $	Change in magnitude of the differential output voltage	See Figure 1 and Figure 2	-0.2	0	0.2	V
$V_{OC(ss)}$	Steady-state common-mode output voltage	See Figure 3	1	2.6	3	V
$\Delta V_{OC(ss)}$	Change in steady-state common-mode output voltage		-0.1		0.1	
$V_{OC(pp)}$	Peak-to-peak common-mode output voltage	See Figure 3		0.5		V
I_I	Input current	D, DE, V_I at 0 V or V_{CC1}	-10	10		μA
I_{OZ}	High-impedance state output current	ISO15	See receiver input current			
		ISO35	V_Y or $V_Z = 12 \text{ V}$	Other input at 0 V	90	μA
			V_Y or $V_Z = 12 \text{ V}$, $V_{CC} = 0$		90	
			V_Y or $V_Z = -7 \text{ V}$		-10	
			V_Y or $V_Z = -7 \text{ V}$, $V_{CC} = 0$		-10	
I_{OS}	Short-circuit output current	V_A or V_B at -7 V	Other input at 0 V	-250	250	mA
		V_A or V_B at 12 V				
C_{OD}	Differential output capacitance	$V_I = 0.4 \sin(4E6\pi t) + 0.5 \text{ V}$, DE at 0 V		16		pF
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 V , See Figure 12 and Figure 13	25	50		kV/ μs

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay	See Figure 4		340		ns
$t_{sk(p)}$	Pulse skew ($ t_{PHL} - t_{PLH} $)			6		
t_r, t_f	Differential output signal rise time, fall time	ISO15 and ISO35	120	180	300	
		ISO15M and ISO35M	120	180	350	
t_{PHZ}	Propagation delay, high-level-to-high-impedance output	See Figure 5		205		ns
t_{PZH}	Propagation delay, high-impedance-to-high-level output			530		
t_{PLZ}	Propagation delay, low-level to high-impedance output	See Figure 6		330		ns
				530		
t_{PZL}	Propagation delay, standby-to-low-level output					

RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{IT(+)}$	Positive-going input threshold voltage	$I_O = -8 \text{ mA}$				-20	mV
$V_{IT(-)}$	Negative-going input threshold voltage	$I_O = 8 \text{ mA}$		-200			mV
V_{hys}	Hysteresis voltage ($V_{IT+} - V_{IT-}$)				50		mV
V_O	Output voltage	$V_{ID} = 200 \text{ mV}$, See Figure 7	$I_O = -8 \text{ mA}$	2.4			V
			$I_O = 8 \text{ mA}$		0.4		
I_{OZ}	High-impedance state output current	$V_I = -7 \text{ to } 12 \text{ V}$, Other input = 0 V		-1	1		μA
I_A or I_B	Bus input current	$-55^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$	V_A or $V_B = 12 \text{ V}$		50	100	μA
			V_A or $V_B = 12 \text{ V}$, $V_{CC} = 0$		50	100	
		$85^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$	V_A or $V_B = 12 \text{ V}$		200		
			V_A or $V_B = 12 \text{ V}$, $V_{CC} = 0$		200		
		$-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$	V_A or $V_B = -7 \text{ V}$	-100	-40		
			V_A or $V_B = -7 \text{ V}$, $V_{CC} = 0$	-100	-30		
I_{IH}	High-level input current, \overline{RE}	$V_{IH} = 2 \text{ V}$		-10			μA
I_{IL}	Low-level input current, \overline{RE}	$V_{IL} = 0.8 \text{ V}$		-10			μA
R_{ID}	Differential input resistance	A, B			48		$\text{k}\Omega$
C_{ID}	Differential input capacitance	$V_I = 0.4 \sin(4E6\pi t) + 0.5V$, DE at 0 V			16		pF

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
t_{PLH}, t_{PHL}	Propagation delay	ISO15x and ISO35x	See Figure 8		100		ns	
$t_{SK(p)}$	Pulse skew ($ t_{PHL} - t_{PLH} $)	ISO15 and ISO35			13			
		ISO15M and ISO35M			18			
		ISO15 and ISO35		2	4			
t_r, t_f	Output signal rise and fall time	ISO15M and ISO35M		2	6			
t_{PZH}, t_{PZL}	Propagation delay, high-impedance-to-high-level output Propagation delay, high-impedance-to-low-level output	DE at 0 V, See Figure 9 and Figure 10		13	25		ns	
				13	25			
t_{PHZ}, t_{PLZ}	Propagation delay, high-level-to-high-impedance output Propagation delay, low-level to high-impedance output							

PARAMETER MEASUREMENT INFORMATION

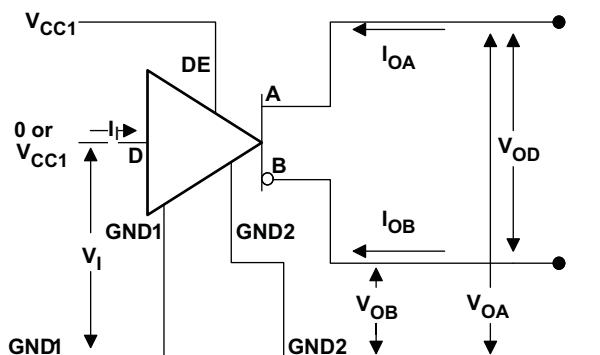


Figure 1. Driver V_{OD} Test and Current Definitions

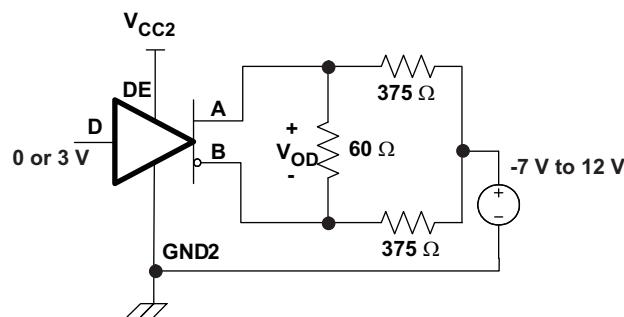


Figure 2. Driver V_{OD} With Common-Mode Loading Test Circuit

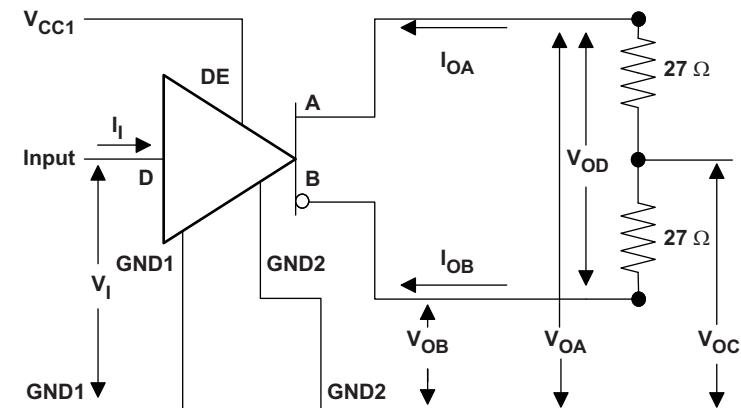
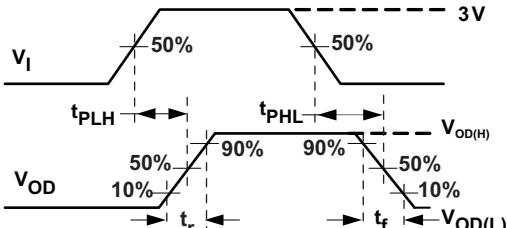


Figure 3. Test Circuit and Waveform Definitions For The Driver Common-Mode Output Voltage



Generator: PRR = 500 kHz, 50% duty cycle, $t_r < 6\text{ ns}$, $t_f < 6\text{ ns}$, $Z_O = 50 \Omega$

C_L includes fixture and Instrumentation Capacitance

Figure 4. Driver Switching Test Circuit and Voltage Waveforms

NOTE: Driver output pins are A and B for the ISO15 (See Figure 1 through Figure 4). These correspond to ISO35 pins Y and Z

PARAMETER MEASUREMENT INFORMATION (continued)

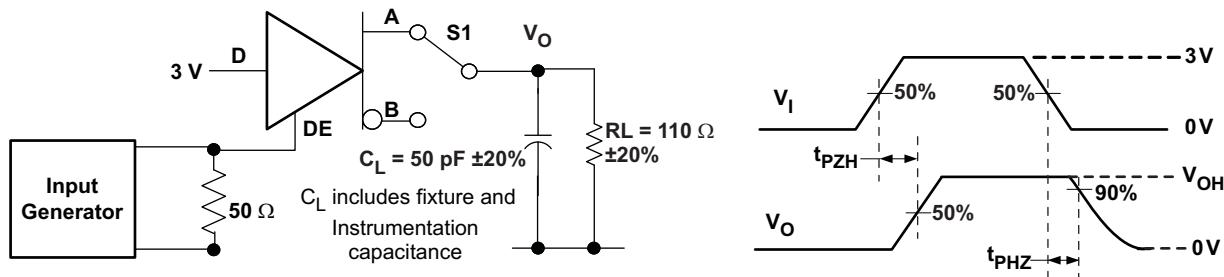


Figure 5. Driver High-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms

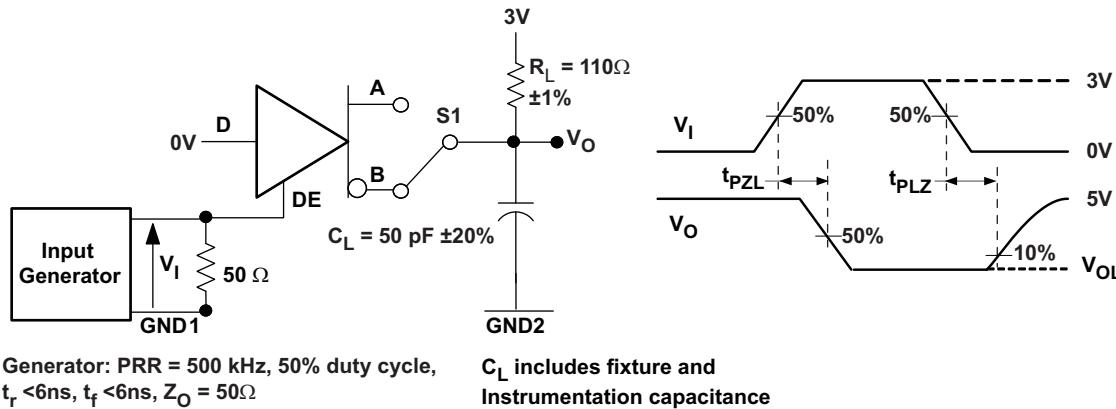


Figure 6. Driver Low-Level Output Enable and Disable Time Test Circuit and Voltage Waveform

NOTE: Driver output pins are A and B for the ISO15 (See [Figure 5](#) through [Figure 6](#)). These correspond to ISO35 pins Y and Z

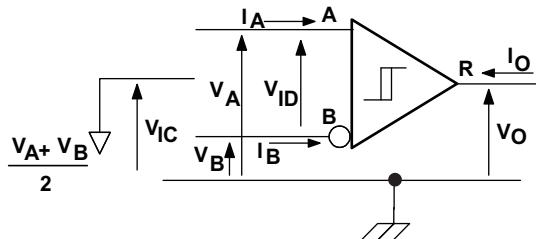


Figure 7. Receiver Voltage and Current Definitions

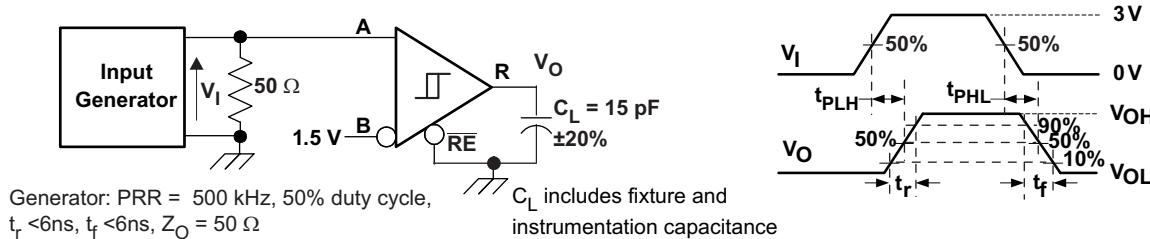


Figure 8. Receiver Switching Test Circuit and Waveforms

PARAMETER MEASUREMENT INFORMATION (continued)

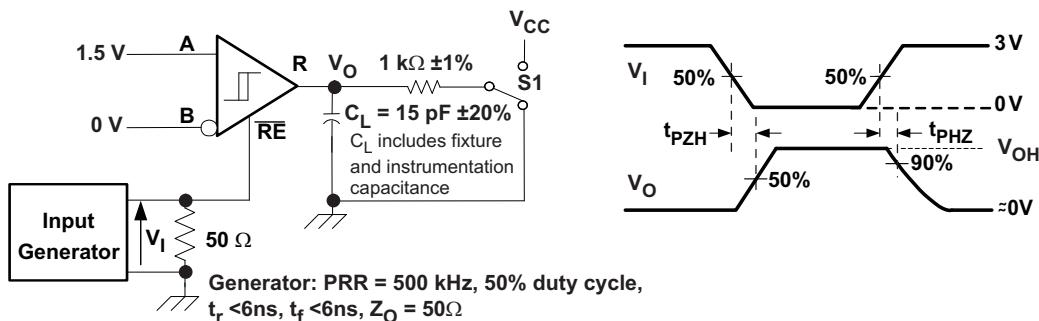


Figure 9. Receiver Enable Test Circuit and Waveforms, Data Output High

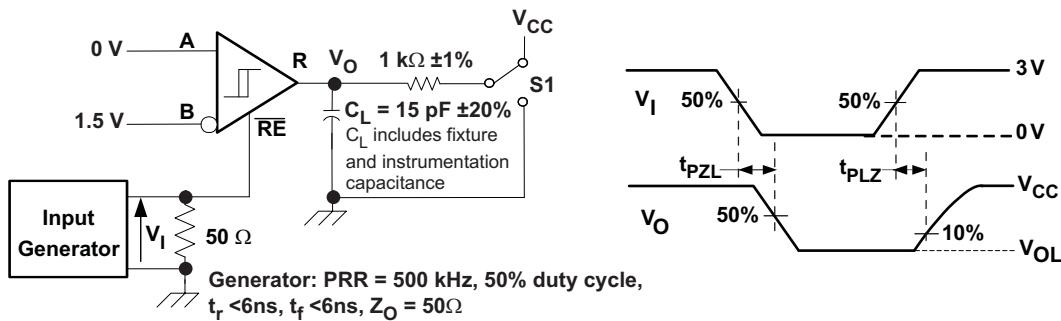
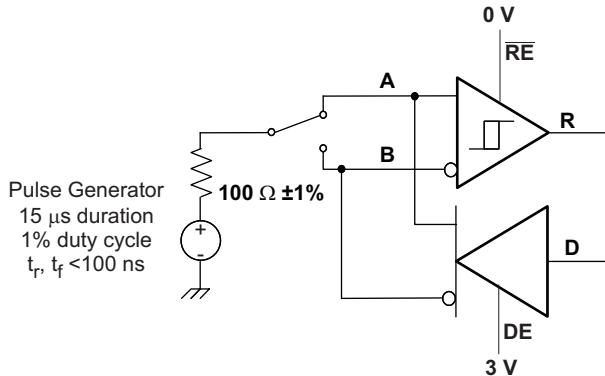


Figure 10. Receiver Enable Test Circuit and Waveforms, Data Output Low



Note: This test is conducted to test survivability only.
Data stability at the R output is not specified.

Figure 11. Transient Over-Voltage Test Circuit

PARAMETER MEASUREMENT INFORMATION (continued)

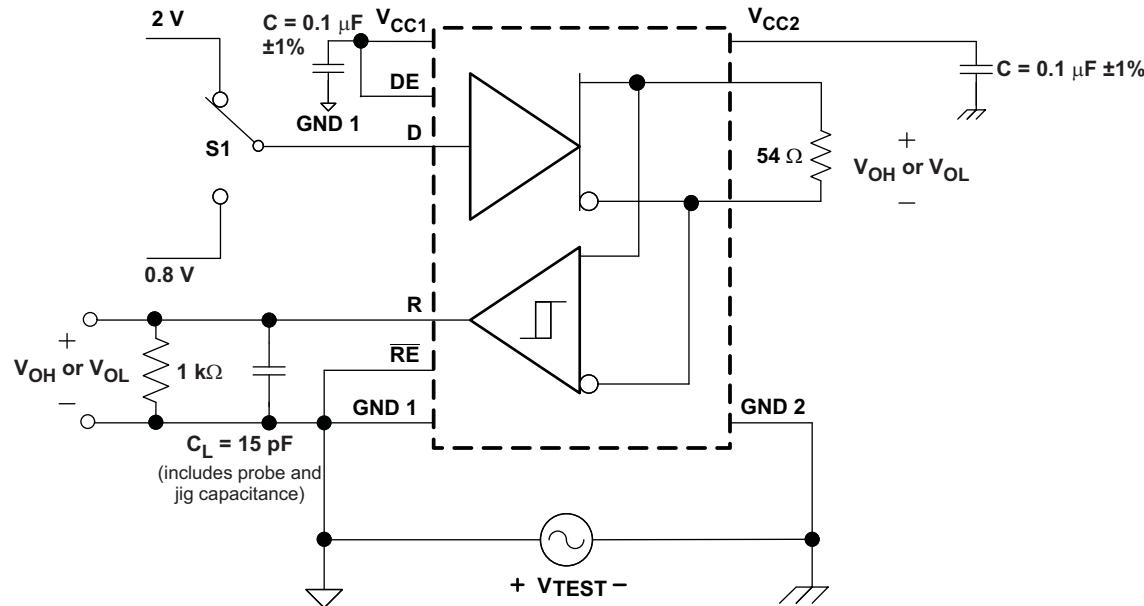


Figure 12. Half-Duplex Common-Mode Transient Immunity Test Circuit

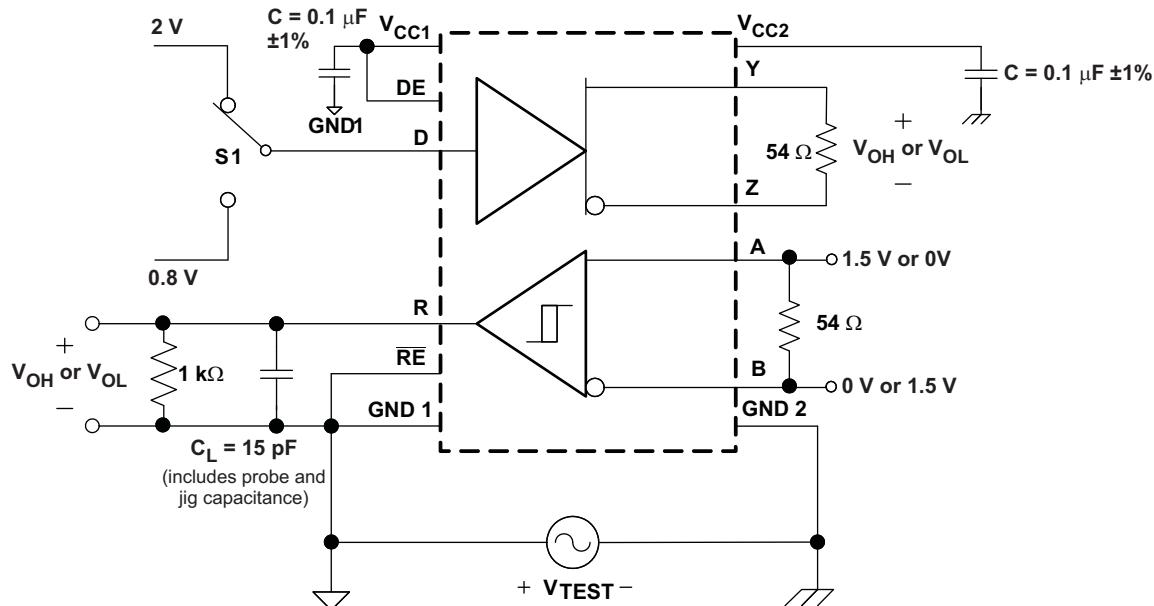


Figure 13. Full-Duplex Common-Mode Transient Immunity Test Circuit

DEVICE INFORMATION

Table 1. Driver Function Table

V_{CC1} ⁽¹⁾	V_{CC2} ⁽¹⁾	INPUT (D)	ENABLE INPUT (DE)	OUTPUTS	
				A or Y	B or Z
PU	PU	H	H	H	L
PU	PU	L	H	L	H
PU	PU	X	L	Z	Z
PU	PU	X	OPEN	Z	Z
PU	PU	OPEN	H	H	L
PD	PU	X	X	Z	Z
PU	PD	X	X	Z	Z
PD	PD	X	X	Z	Z

(1) PU = Power Up, PD = Power Down

Table 2. Receiver Function Table

V_{CC1} ⁽¹⁾	V_{CC2} ⁽¹⁾	DIFFERENTIAL INPUT $V_{ID} = (V_A - V_B)$	ENABLE (RE)	OUTPUT (®)
PU	PU	$-0.01 \text{ V} \leq V_{ID}$	L	H
PU	PU	$-0.2 \text{ V} < V_{ID} < -0.01 \text{ V}$	L	?
PU	PU	$V_{ID} \leq -0.2 \text{ V}$	L	L
PU	PU	X	H	Z
PU	PU	X	OPEN	Z
PU	PU	Open circuit	L	H
PU	PU	Short Circuit	L	H
PU	PU	Idle (terminated) bus	L	H
PD	PU	X	X	Z
PU	PD	X	L	H

(1) PU = Power Up, PD = Power Down

PACKAGE CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER ⁽¹⁾	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01) Minimum air gap (Clearance)	Shortest terminal to terminal distance through air	8.34			mm
L(I02) Minimum external tracking (Creepage)	Shortest terminal to terminal distance across the package surface	8.1			mm
CTI Tracking resistance (Comparative Tracking Index)	DIN IEC 60112 / VDE 0303 Part 1	≥400			V
Minimum Internal Gap (Internal Clearance)	Distance through the insulation	0.008			mm
R _{IO} Isolation resistance	Input to output, V _{IO} = 500 V, all pins on each side of the barrier tied together creating a two-terminal device		>10 ¹²		Ω
C _{IO} Barrier capacitance Input to output	V _I = 0.4 sin (4E6πt)		2		pF
C _I Input capacitance to ground	V _I = 0.4 sin (4E6πt)		2		pF

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board do not reduce this distance. Creepage and clearance on a printed circuit board become equal according to the measurement techniques shown in the Isolation Glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

IEC 60664-1 RATINGS TABLE

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	II
Installation classification	Rated mains voltage ≤ 150 V _{RMS}	I-IV
	Rated mains voltage ≤ 300 V _{RMS}	I-III
	Rated mains voltage ≤ 400 V _{RMS}	I-II

IEC 60747-5-2 INSULATION CHARACTERISTICS⁽¹⁾

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	SPECIFICATION	UNIT
V _{IORM}	Maximum working insulation voltage	560	V
V _{PR}	Input to output test voltage	1050	V
V _{IOTM}	Transient overvoltage	4000	V
R _S	Insulation resistance	>10 ⁹	Ω
	Pollution degree	2	

- (1) Climatic Classification 40/125/21

REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2	Approved under CSA Component Acceptance Notice 5A	Recognized under 1577 Component Recognition Program
Basic Insulation Maximum Transient Overvoltage, 4000 V _{PK} Maximum Surge Voltage, 4000 V _{PK} Maximum Working Voltage, 560 V _{PK}	2500 V _{RMS} rating per CSA 60950-1-07 and IEC 60950-1 (2nd Ed.) for products with working voltages ≤ 280 V _{RMS} for basic insulation.	Single Protection, 2500 V _{RMS}
File Number: 40016131	File Number: 220991	File Number: E181974

IEC SAFETY LIMITING VALUES

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the IO can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier potentially leading to secondary system failures.

PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	
I_S Safety input, output, or supply current	DW-16	$\theta_{JA} = 212^\circ\text{C/W}$, $V_I = 5.5 \text{ V}$, $T_J = 170^\circ\text{C}$, $T_A = 25^\circ\text{C}$		210		mA	
T_S Maximum case temperature	DW-16			150		°C	

The safety-limiting constraint is the absolute maximum junction temperature specified in the absolute maximum ratings table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the Thermal Characteristics table is that of a device installed in the JESD51-3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

THERMAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
θ_{JA} Junction-to-Air	Low-K Thermal Resistance ⁽¹⁾	168		96.1	°C/W	
	High-K Thermal Resistance	96.1				
θ_{JB} Junction-to-Board Thermal Resistance		61		°C/W		
θ_{JC} Junction-to-Case Thermal Resistance		48		°C/W		
P_D Device Power Dissipation	$V_{CC1} = V_{CC2} = 5.25 \text{ V}$, $T_J = 150^\circ\text{C}$, $C_L = 15 \text{ pF}$, Input a 20 MHz 50% duty cycle square wave	220		mW		

(1) Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages.

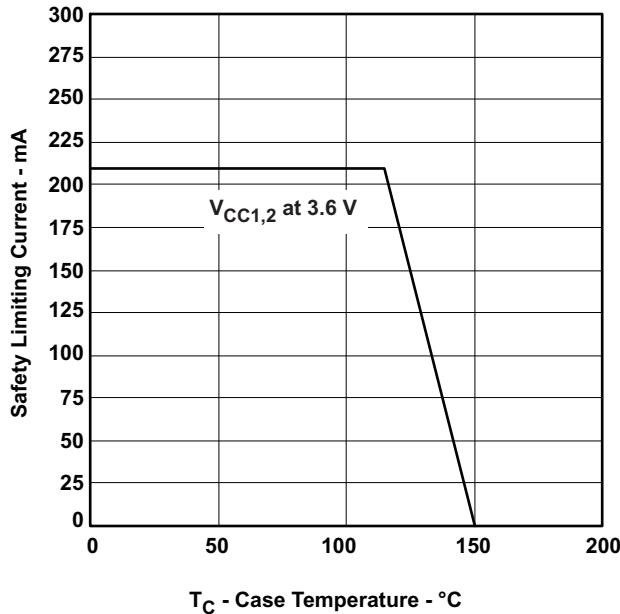
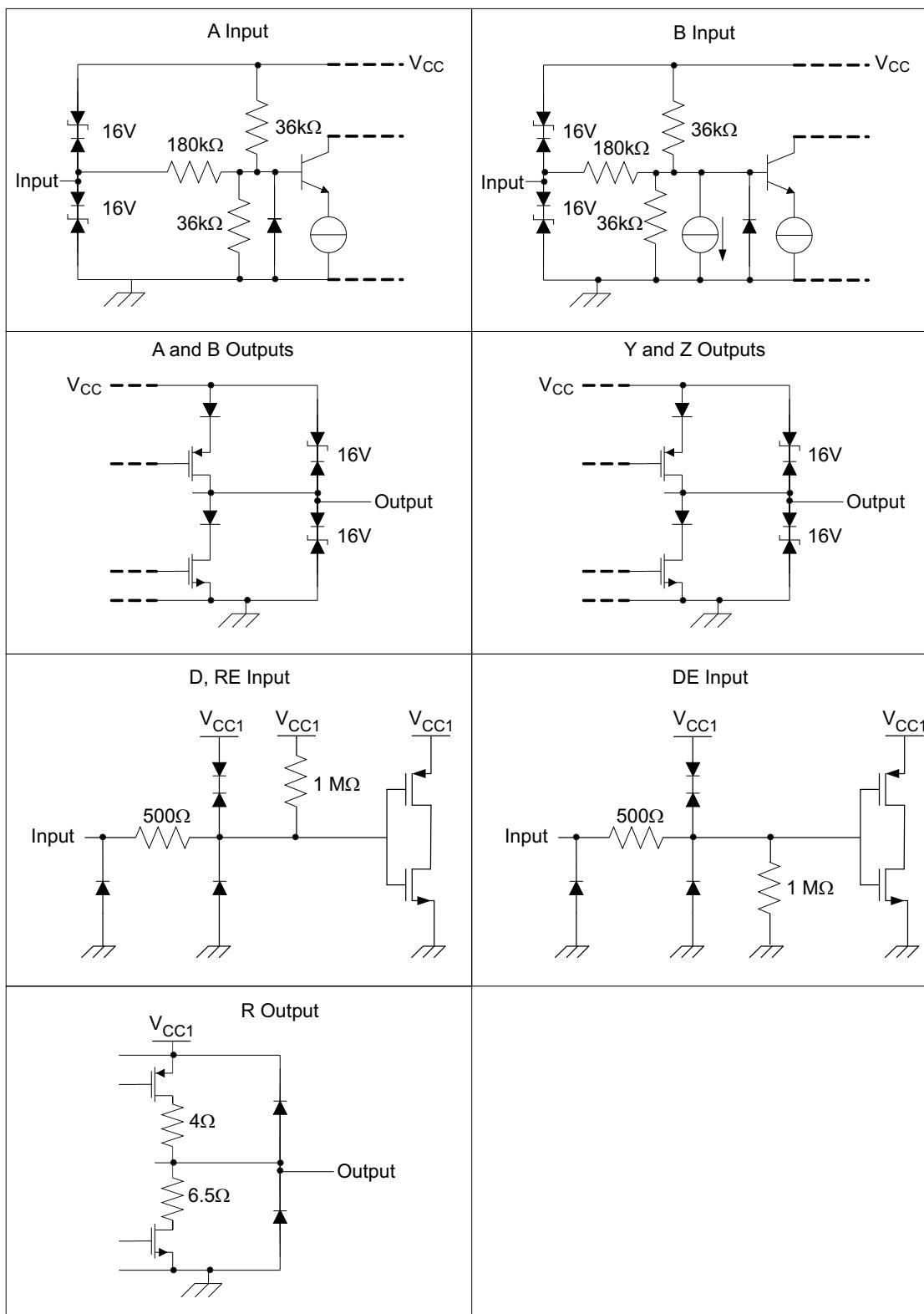


Figure 14. DW-16 θ_{JC} Thermal Derating Curve per IEC 60747-5-2

EQUIVALENT CIRCUIT SCHEMATICS



TYPICAL CHARACTERISTICS CURVES

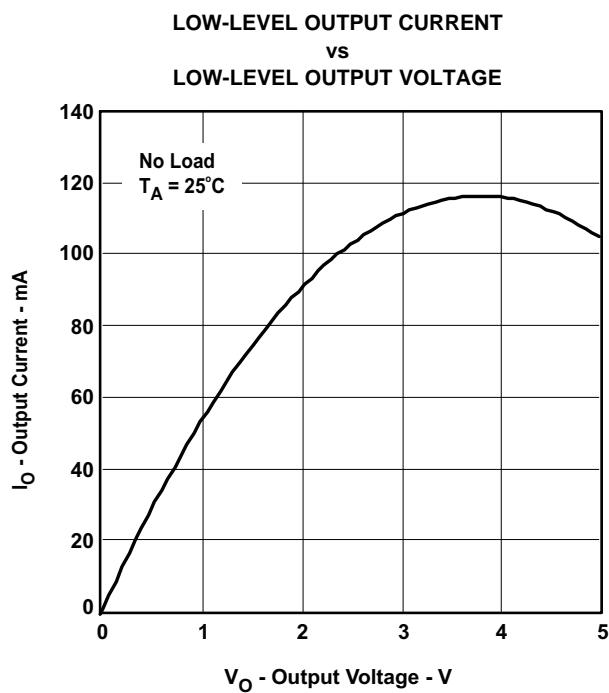


Figure 15.



Figure 16.

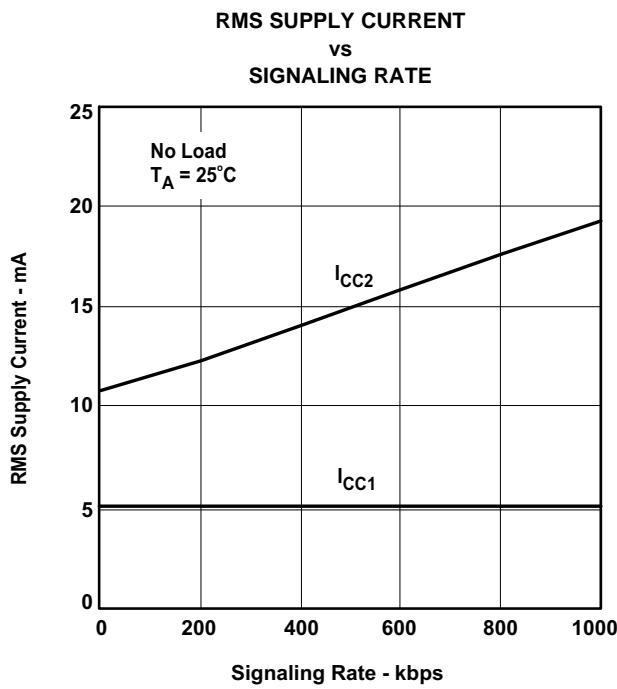


Figure 17.

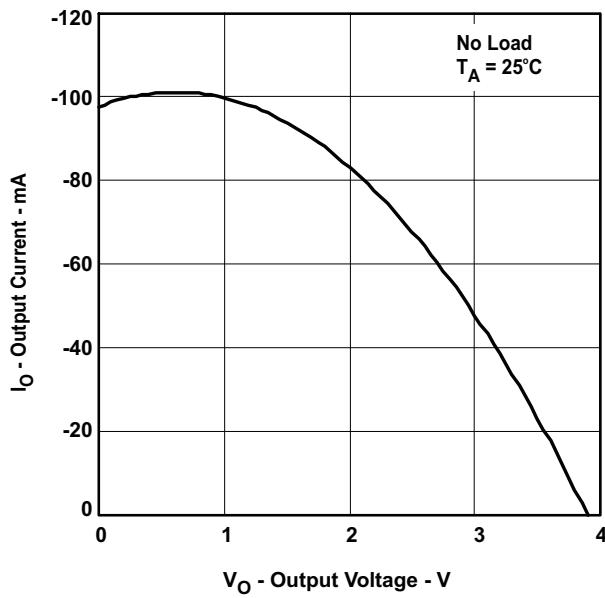


Figure 18.

TYPICAL CHARACTERISTICS CURVES (continued)

DRIVER DIFFERENTIAL OUTPUT VOLTAGE
vs
FREE-AIR TEMPERATURE

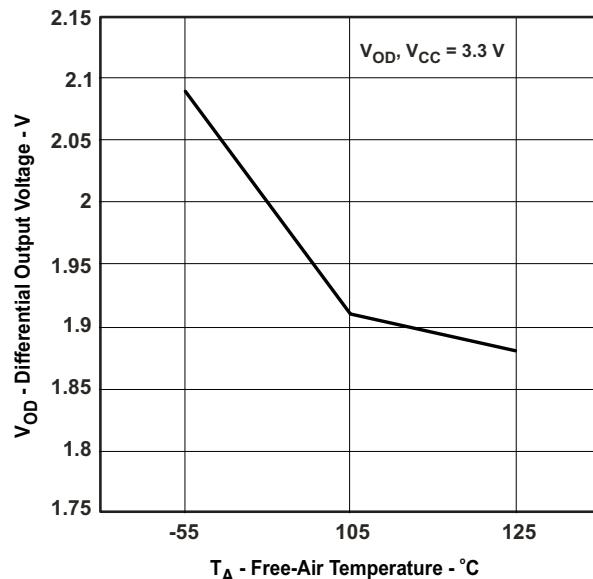


Figure 19.

DRIVER PROPAGATION DELAY
vs
FREE-AIR TEMPERATURE

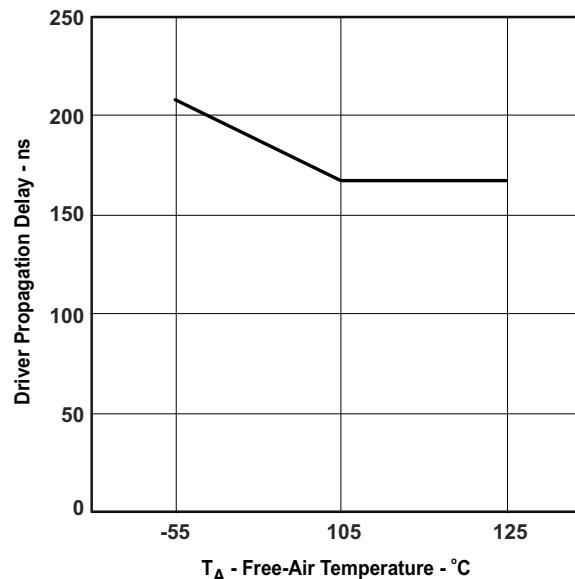


Figure 20.

APPLICATION INFORMATION

Transient Voltages

Isolation of a circuit insulates it from other circuits and earth so that noise develops across the insulation rather than circuit components. The most common noise threat to data-line circuits is voltage surges or electrical fast transients that occur after installation. The transient ratings of the ISO15 and ISO35 are sufficient for all but the most severe installations. However, some equipment manufacturers use their ESD generators to test transient susceptibility of their equipment, and can exceed insulation ratings. ESD generators simulate static discharges that may occur during device or equipment handling with low-energy but high voltage transients.

Figure 21 models the ISO15 and ISO35 bus IO connected to a noise generator. C_{IN} and R_{IN} is capacitance or resistance across the device and any other stray or added capacitance or resistance across the A or B pin to GND2. C_{ISO} and R_{ISO} is the capacitance and resistance between GND1 and GND2 of the ISO15 and ISO35 plus those of any other insulation (transformer, etc.). The stray inductance is assumed to be negligible. From this model, the voltage at the isolated bus return is,

$$V_{GND2} = V_N \frac{Z_{ISO}}{Z_{ISO} + Z_{IN}} \quad (1)$$

and will always be less than 16 V from V_N . If the ISO15 and ISO35 are tested as a stand-alone device, $R_{IN} = 6 \times 10^4 \Omega$, $C_{IN} = 16 \times 10^{-12} F$, $R_{ISO} = 10^9 \Omega$ and $C_{ISO} = 10^{-12} F$.

Note from **Figure 21** that the resistor ratio determines the voltage ratio at low frequency and it is the inverse capacitance ratio at high frequency. In the stand-alone case and for low frequency,

$$\frac{V_{GND2}}{V_N} = \frac{R_{ISO}}{R_{ISO} + R_{IN}} = \frac{10^9}{10^9 + 6 \times 10^4} \quad (2)$$

or essentially all of noise appears across the barrier. At high frequency,

$$\frac{V_{GND2}}{V_N} = \frac{\frac{1}{C_{ISO}}}{\frac{1}{C_{ISO}} + \frac{1}{C_{IN}}} = \frac{1}{1 + \frac{C_{ISO}}{C_{IN}}} = \frac{1}{1 + \frac{1}{16}} = 0.94 \quad (3)$$

and 94% of V_N appears across the barrier. As long as R_{ISO} is greater than R_{IN} and C_{ISO} is less than C_{IN} , most of transient noise appears across the isolation barrier.

It is not recommended for the user to test equipment transient susceptibility with ESD generators, or consider product claims of ESD ratings above the barrier transient ratings of an isolated interface. ESD is best managed through recessing or covering connector pins in a conductive connector shell and installer training.

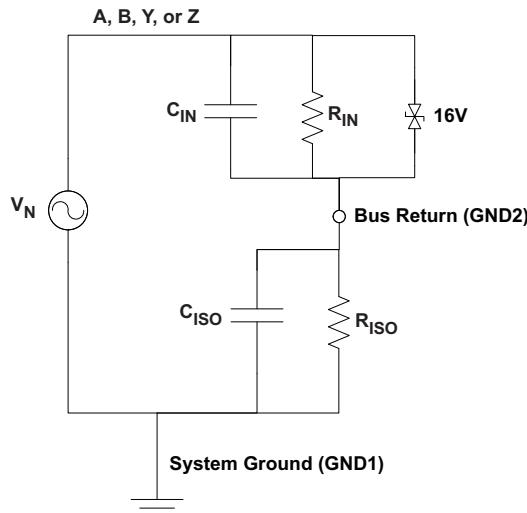


Figure 21. Noise Model

REVISION HISTORY

Changes from Original (May 2008) to Revision A	Page
• Changed L(101) Minimum air gap (Clearance) From 7.7mm To 8.34mm.	10
• Deleted CSA information from the Regulatory Information Table.	10
• Changed From 40014131 To 40016131	10

Changes from Revision A (June 2008) to Revision B	Page
• Changed From: 4000-Vpeak Isolation To: 4000-Vpeak Isolation, 560-Vpeak VIORM UL 1577, IEC 60747-5-2 (VDE 0884, Rev 2)	1
• Changed Figure 13 , Full-Duplex Common-Mode Transient Immunity Test Circuit	8

Changes from Revision B (July 2008) to Revision C	Page
• Added added IEC.....Approved	1
• Added added CSA information column back in table	10

Changes from Revision C (December 2008) to Revision D	Page
• Changed Propagation delay values From: μ s To: ns in the DRIVER SWITCHING table	3

Changes from Revision D (March 2009) to Revision E	Page
• Added devices ISO15M and ISO35M to the data sheet	1
• Changed Description - From: The ISO15 and ISO35 are qualified for use from -40°C to 85°C . To: The ISO15M and ISO35M have extended ambient temperature ratings of -55°C to 125°C while the ISO15 and ISO35 are specified over -40°C to 85°C .	1
• Added the Product Information table	1
• Added Added Ambient Temp information in the RECOMMENDED OPERATING CONDITIONS table	2
• Added ISO15M and ISO35M to the Operating junction temperature in the RECOMMENDED OPERATING CONDITIONS table	2
• Changed the DRIVER ELECTRICAL table, I_{OZ} High-impedance state output current - Test Condition V_Y or $V_Z = 12\text{ V}$, $V_{CC} = 0$ values From: TYP = -10 , MAX = - To: TYP = -, MAX = 90.	3
• Changed the DRIVER ELECTRICAL table, I_{OZ} High-impedance state output current - Test Condition V_Y or $V_Z = -7\text{ V}$ values From: TYP = -, MAX = 90 To: TYP = -10, MAX = -	3
• Added t_r , t_f limits for the ISO15M ans ISO35M devices	3
• Added I_A or I_B limits for the ISO15M ans ISO35M devices	4
• Added pulse skew limits for the ISO15M ans ISO35M devices	4
• Added t_r , t_f for the ISO15M ans ISO35M devices	4
• Added the Driver output pins Note for Figure 1 through Figure 4	5
• Changed the Driver output pins Note for eFigure 5 through Figure 6	6
• Added Note 1 to Table 1 Driver Function Table	9
• Added Note 1 to Table 2 Receiver Function Table	9
• Changed Figure 19 - replaced curves	14
• Changed Figure 20 - replaced curves	14

Changes from Revision E (April 2010) to Revision F**Page**

• Changed the FEATURES From: 4000-V _{peak} 560-V _{peak} V _{IORM} per IEC....Rev 2) To: 4000-V _{PK} V _{IOTM} , 560-V _{PK} V _{IORM} , IEC 60747-5-2 (VDE 0884, Rev 2)	1
• Changed Description From: The symmetrical isolation.....interface. To; The symmetrical isolation barrier of the device is tested to provide isolatlon of 4000 V _{PK} per VDE and 2500 V _{RMS} per UL and CSA betweeninterface.	1
• Changed CTI From: ≥ 175 V To: ≥ 400 V	10
• Changed the IEC Ratings table, Basic isolation group, specification from IIIa to II	10
• Changed the Regulatory Information Table	10

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾	Op Temp (°C)	Top-Side Markings ⁽⁴⁾	Samples
ISO15DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO15	Samples
ISO15DWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO15	Samples
ISO15DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO15	Samples
ISO15DWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO15	Samples
ISO15MDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO15M	Samples
ISO15MDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO15M	Samples
ISO35DW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO35	Samples
ISO35DWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO35	Samples
ISO35DWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO35	Samples
ISO35DWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO35	Samples
ISO35MDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO35M	Samples
ISO35MDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO35M	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

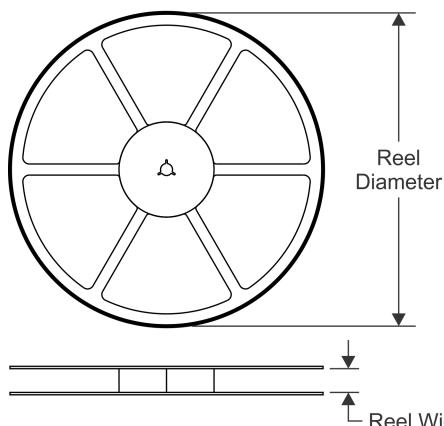
(4) Only one of markings shown within the brackets will appear on the physical device.

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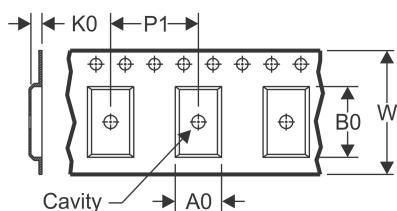
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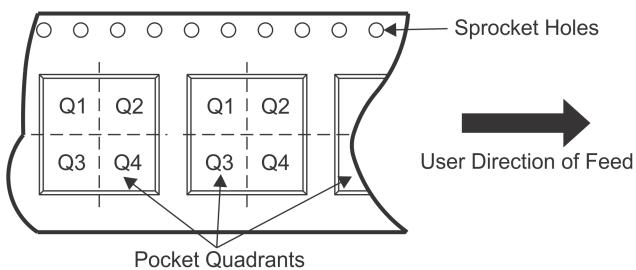


TAPE DIMENSIONS



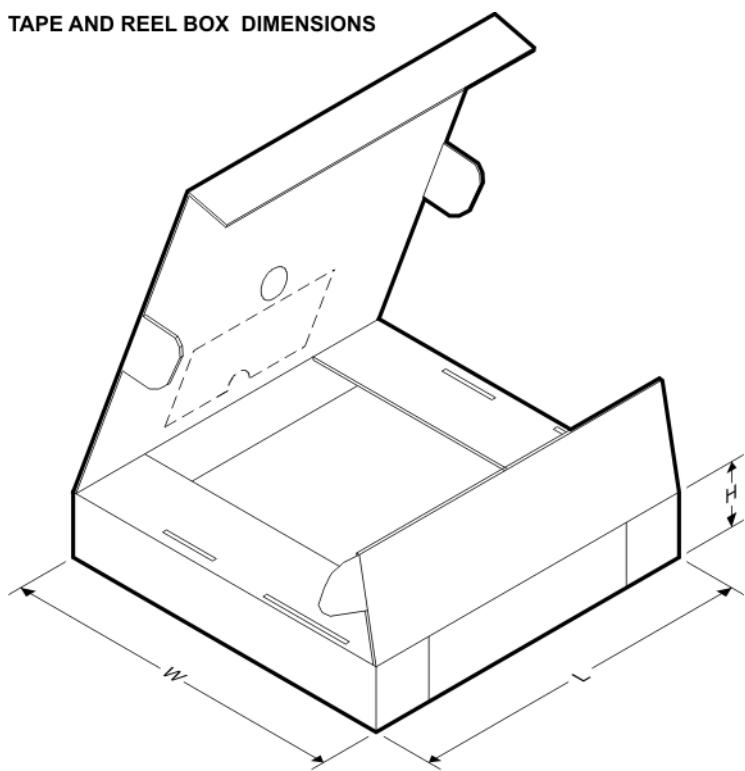
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO15MDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO35DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO35MDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS


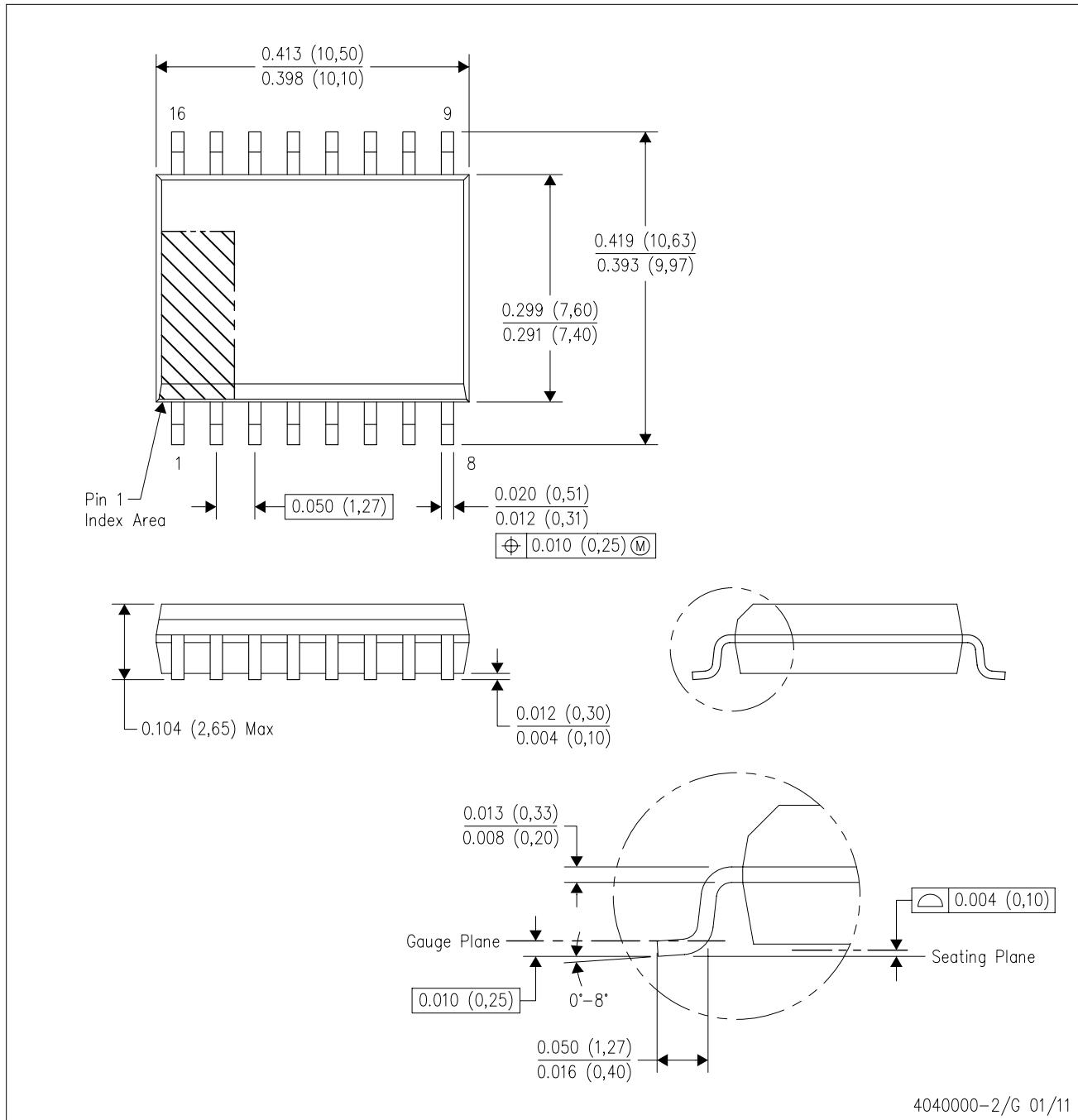
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO15MDWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO35DWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO35MDWR	SOIC	DW	16	2000	367.0	367.0	38.0

MECHANICAL DATA

DW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



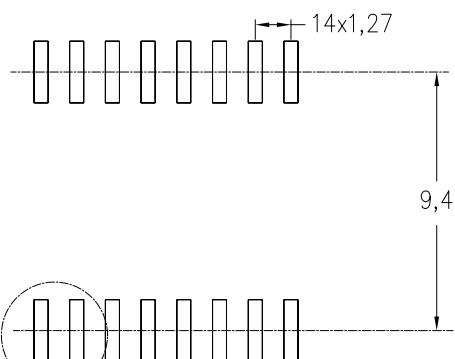
- NOTES:
- All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0.15).
 - Falls within JEDEC MS-013 variation AA.

LAND PATTERN DATA

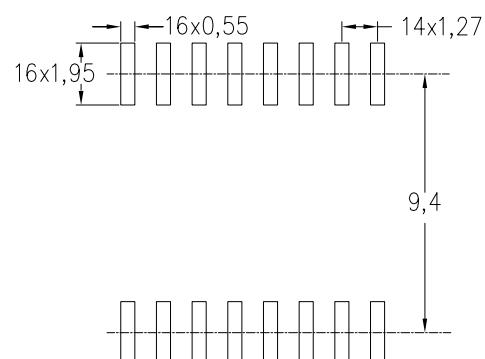
DW (R-PDSO-G16)

PLASTIC SMALL OUTLINE

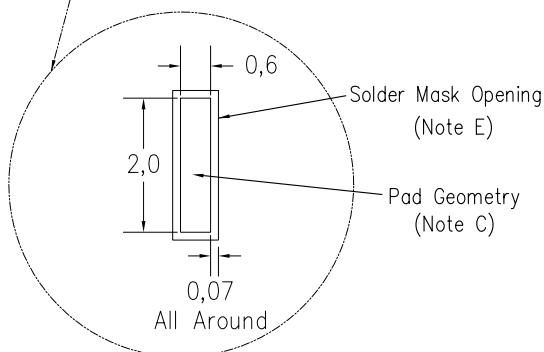
Example Board Layout
(Note C)



Stencil Openings
(Note D)



Non Solder Mask Define Pad



4209202-2/E 07/11

- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Refer to IPC7351 for alternate board design.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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